

MMBD914

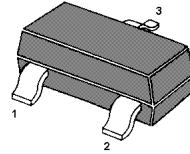
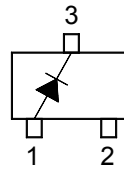
Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application



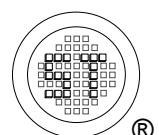
Marking Code: **5D**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	100	V
Forward Current	I_F	200	mA
Non-repetitive Peak Forward Surge Current ($t = 1\ \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\ \text{mA}$	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	100	-	V
Reverse Current at $V_R = 20\ \text{V}$ at $V_R = 75\ \text{V}$	I_R	- -	25 5	nA μA
Reverse Recovery Time at $I_F = I_R = 10\ \text{mA}$	t_{rr}	-	4	ns
Total Capacitance at $V_R = 0$, $f = 1\ \text{MHz}$	C_T	-	4	pF



Dated : 15/06/2009

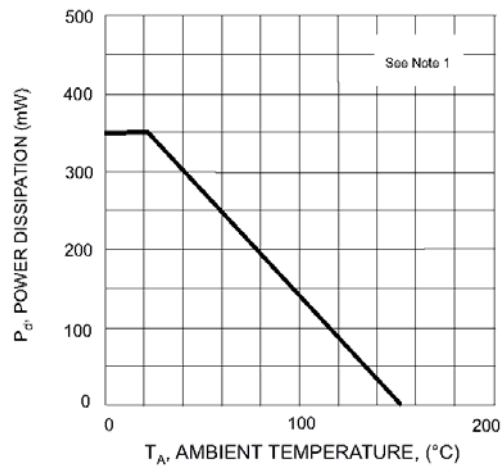


Fig. 1 Power Derating Curve

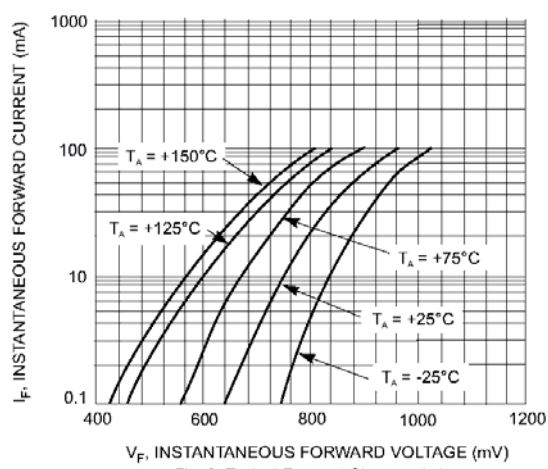


Fig. 2 Typical Forward Characteristics

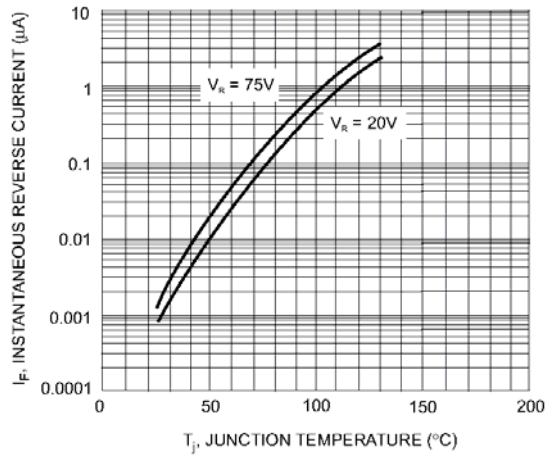


Fig. 3 Typical Reverse Characteristics

